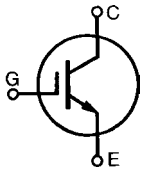
IXYS

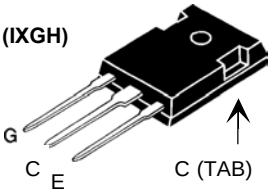
HiPerFAST™ IGBT

IXGH 50N60B
IXGK 50N60B
IXGT 50N60B
IXGJ 50N60B

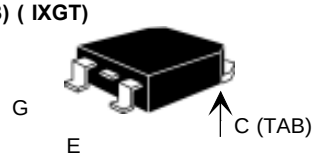
V_{CES} = 600 V
I_{C25} = 75 A
$V_{CE(sat)}$ = 2.3 V
$t_{fi(typ)}$ = 120 ns



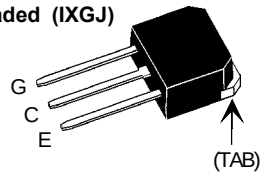
TO-247 AD (IXGH)



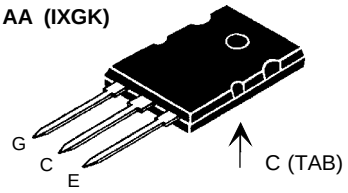
TO-268 (D3) (IXGT)



TO-268 Leaded (IXGJ)



TO-264 AA (IXGK)



Symbol	Test Conditions		Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C		600	V
V_{CGR}	T_J = 25°C to 150°C; R_{GE} = 1 MΩ		600	V
V_{GES}	Continuous		±20	V
V_{GEM}	Transient		±30	V
I_{C25}	T_C = 25°C		75	A
I_{C90}	T_C = 90°C		50	A
I_{CM}	T_C = 25°C, 1 ms		200	A
SSOA (RBSOA)	V_{GE} = 15 V, T_{VJ} = 125°C, R_G = 10 Ω Clamped inductive load		I_{CM} = 100 @ 0.8 V_{CES}	A
P_C	T_C = 25°C		300	W
T_J			-55 ... +150	°C
T_{JM}			150	°C
T_{stg}			-55 ... +150	°C
M_d	Mounting torque	TO-247AD TO-264	1.13/10 0.9/6	Nm/lb.in. Nm/lb.in.
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s			300	°C
Weight		TO-247 TO-264 TO-268	6 10 4	g g g

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) Min.	Typ.	Max.	
BV_{CES}	I_C = 250μA, V_{GE} = 0 V		600			V
$V_{GE(th)}$	I_C = 250 μA, V_{CE} = V_{GE}		2.5		5.0	V
I_{CES}	V_{CE} = 0.8 • V_{CES} V_{GE} = 0 V	T_J = 25°C T_J = 125°C			200 1	μA mA
I_{GES}	V_{CE} = 0 V, V_{GE} = ±20 V				±100	nA
$V_{CE(sat)}$	I_C = I_{C90}, V_{GE} = 15 V				2.3	V

G = Gate D = Drain
E = Emitter TAB = Collector

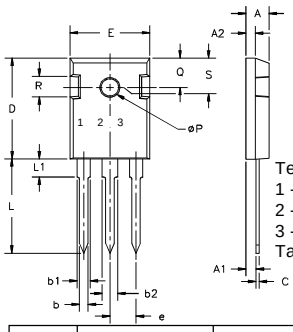
Features
- International standard packages
- High frequency IGBT
- Latest generation HDMOS™ process
- High current handling capability
- MOS Gate turn-on
  - drive simplicity

Applications
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Advantages
- Easy to mount with 1 screw (insulated mounting screw hole)
- Switching speed for high frequency applications
- High power density

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values min.	typ.	max.	
g_{fs}	$I_C = I_{C90}$; V_{CE} = 10 V, Pulse test, t ≤ 300 µs, duty cycle ≤ 2 %	25	42		S
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		4100		pF
C_{oes}			310		pF
C_{res}			95		pF
Q_G	$I_C = I_{C90}$, V_{GE} = 15 V, V_{CE} = 0.5 V_{CES}		160		nC
Q_{GE}			30		nC
Q_{GC}			55		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		50		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V		50		ns
$t_{d(off)}$	V_{CE} = 0.8 • V_{CES}, $R_G = R_{off}$ = 2.7 Ω		150	250	ns
t_{fi}	Remarks: Switching times may increase for V_{CE} (Clamp) > 0.8 • V_{CES}, higher T_J or increased R_G		120	250	ns
E_{off}			3.0	4.5	mJ
$t_{d(on)}$	**Inductive load, T_J = 125°C**		50		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V		50		ns
E_{on}	V_{CE} = 0.8 • V_{CES}, $R_G = R_{off}$ = 2.7 Ω		3		mJ
$t_{d(off)}$	Remarks: Switching times may increase for V_{CE} (Clamp) > 0.8 • V_{CES}, higher T_J or increased R_G		200		ns
t_{fi}			250		ns
E_{off}			4.2		mJ
R_{thJC}				0.42	K/W
R_{thCK}	TO-247 & TO-268 leaded packages		0.25		K/W
	TO-264 package		0.15		K/W

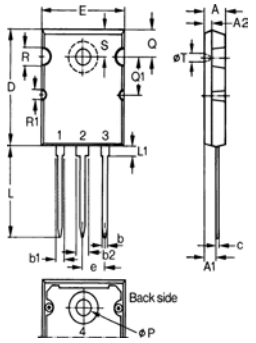
TO-247 AD (IXGH) Outline



Terminals:
1 - Gate
2 - Collector
3 - Emitter
Tab - Collector

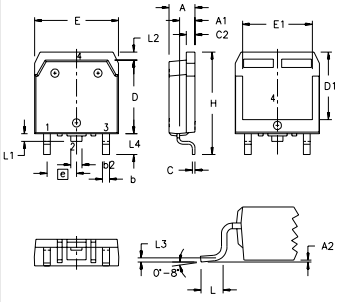
Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

TO-264 AA (IXGK) Outline



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

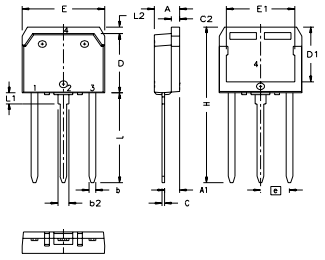
TO-268 (IXGT) Outline



SYM	INCHES MIN	MAX	MILLIMETERS MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

Terminals:
1 - Gate
2 - Collector

TO-268 (IXGJ) Leaded Outline



SYM	INCHES MIN	MAX	MILLIMETERS MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	1.365	1.395	34.67	35.43
L	.780	.800	19.81	20.32
L1	.079	.091	2.00	2.30
L2	.039	.045	1.00	1.15

NOTE: ALL METAL AREA ARE SOLDER PLATED.

1 – GATE
2 – DRAIN (COLLECTOR)
3 – SOURCE (EMITTER)
4 – DRAIN (COLLECTOR)

IXYS reserves the right to change limits, test conditions, and dimensions.

Figure 1. Saturation Voltage Characteristics

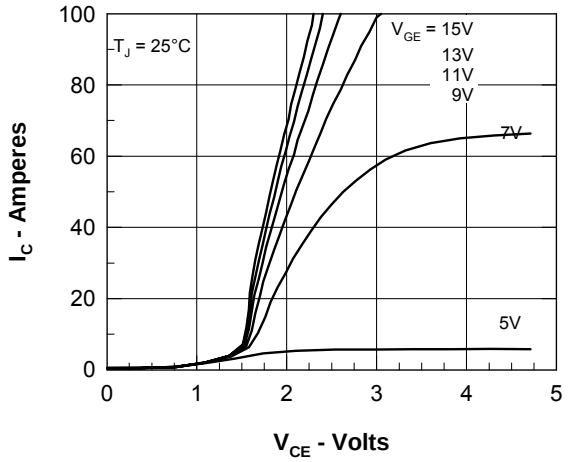


Figure 2. Extended Output Characteristics

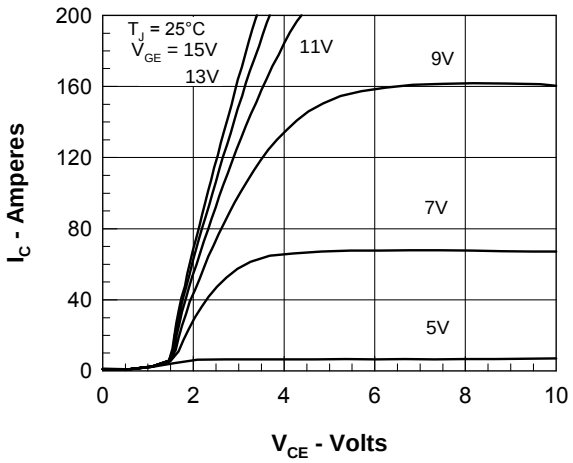


Figure 3. Saturation Voltage Characteristics

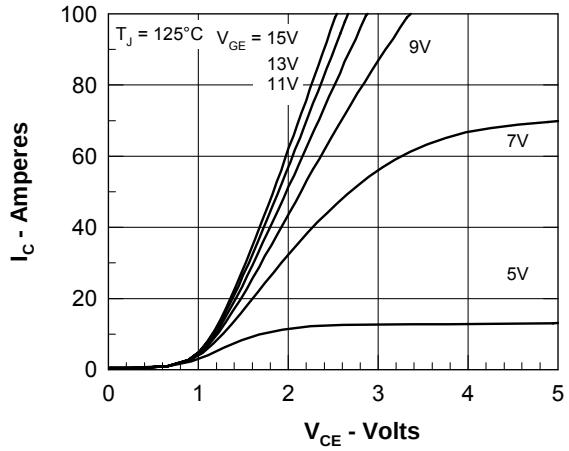


Figure 4. Temperature Dependence of $V_{CE(sat)}$

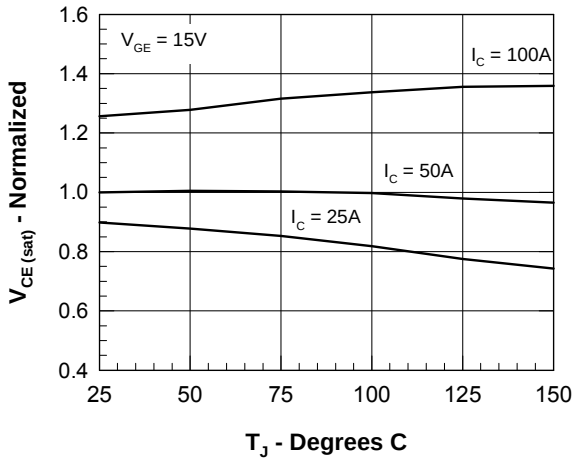


Figure 5. Admittance Curves

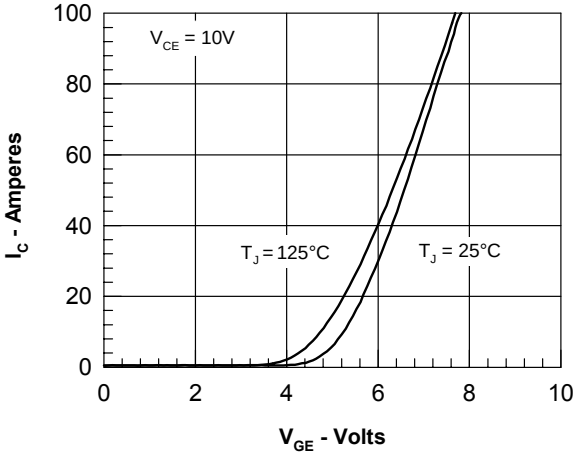


Figure 6. Capacitance Curves

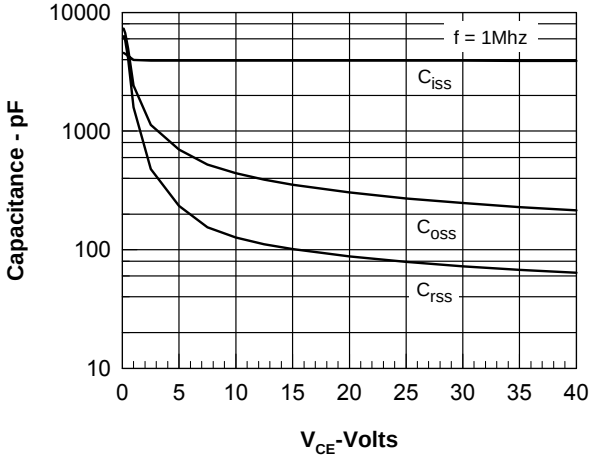


Figure 7. Dependence of E_{ON} and E_{OFF} on I_C

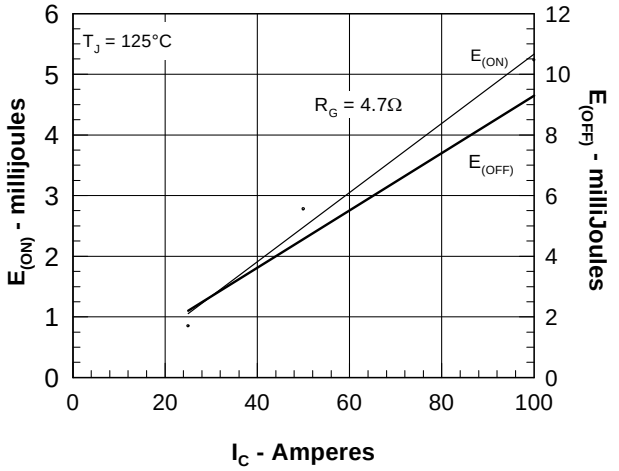


Figure 8. Dependence of E_{ON} and E_{OFF} on R_G

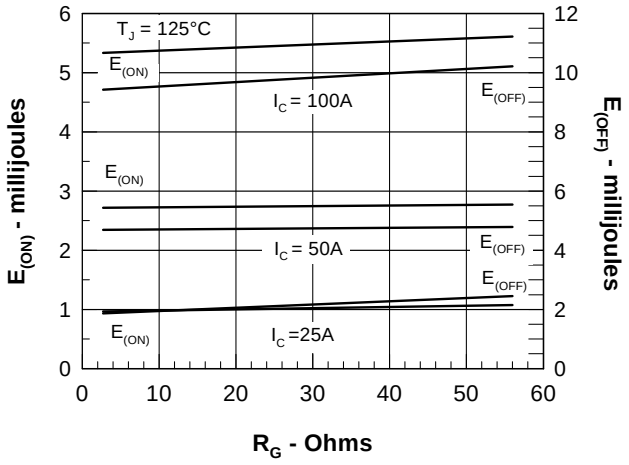


Figure 9. Gate Charge

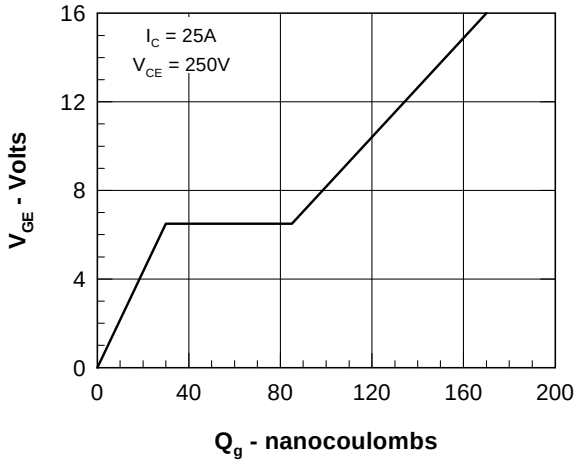


Figure 10. Turn-off Safe Operating Area

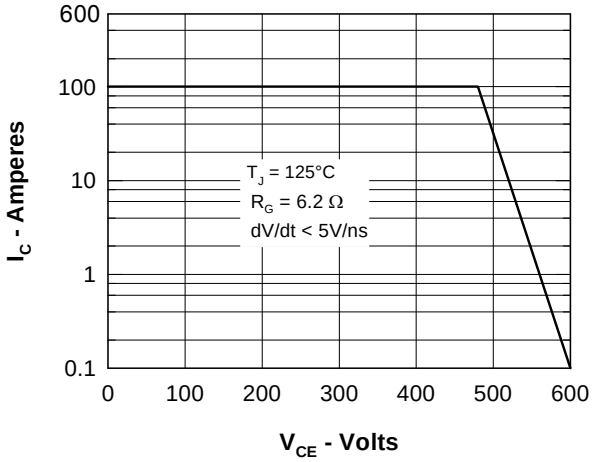


Figure 11. IGBT Transient Thermal Resistance